

	<u>Type</u>	<u>L #</u>	<u>Hits</u>	<u>Search Text</u>	<u>DBs</u>
<u>1</u>	<u>BRS</u>	<u>L1</u>	<u>20272</u>	<u>buffer adj2 (layer or film or layers or films)</u>	<u>US-PGPUB; USPAT</u>
<u>2</u>	<u>BRS</u>	<u>L2</u>	<u>27959</u>	<u>high adj2 dielectric</u>	<u>US-PGPUB; USPAT</u>
<u>3</u>	<u>BRS</u>	<u>L3</u>	<u>0</u>	<u>1 near5 (ald near2 ((silicon adj dioxide) or "SiO.sub.2"))</u>	<u>US-PGPUB; USPAT</u>
<u>4</u>	<u>BRS</u>	<u>L4</u>	<u>2</u>	<u>1 near10 (ald near5 ((silicon adj dioxide) or "SiO.sub.2"))</u>	<u>US-PGPUB; USPAT</u>
<u>5</u>	<u>BRS</u>	<u>L5</u>	<u>1234</u>	<u>1 near5 ((silicon adj dioxide) or "SiO.sub.2")</u>	<u>US-PGPUB; USPAT</u>
<u>6</u>	<u>BRS</u>	<u>L6</u>	<u>5</u>	<u>2 near20 5</u>	<u>US-PGPUB; USPAT</u>
<u>7</u>	<u>BRS</u>	<u>L7</u>	<u>64</u>	<u>(ald near5 ((silicon adj dioxide) or "SiO.sub.2"))</u>	<u>US-PGPUB; USPAT</u>
<u>8</u>	<u>BRS</u>	<u>L8</u>	<u>232</u>	<u>7 near10 "9"(((silicon adj tetrachloride) or "SiCl.sub.4") near3 precursor)</u>	<u>US-PGPUB; USPAT</u>
<u>9</u>	<u>BRS</u>	<u>L9</u>	<u>0</u>	<u>7 near10 (((silicon adj tetrachloride) or "SiCl.sub.4") near3 precursor)</u>	<u>US-PGPUB; USPAT</u>
<u>10</u>	<u>BRS</u>	<u>L10</u>	<u>1</u>	<u>7 same (((silicon adj tetrachloride) or "SiCl.sub.4") near3 precursor)</u>	<u>US-PGPUB; USPAT</u>
<u>11</u>	<u>BRS</u>	<u>L11</u>	<u>232</u>	<u>(((silicon adj tetrachloride) or "SiCl.sub.4") near3 precursor)</u>	<u>US-PGPUB; USPAT</u>

	<u>Type</u>	<u>L #</u>	<u>Hits</u>	<u>Search Text</u>	<u>DBs</u>
<u>12</u>	<u>BRS</u>	<u>L12</u>	<u>39</u>	<u>11 near10 ((silicon adj dioxide) or "SiO.sub.2")</u>	<u>US-PGPUB;</u> <u>USPAT</u>
<u>13</u>	<u>BRS</u>	<u>L13</u>	<u>3</u>	<u>ald same (((silicon adj tetrachloride) or "SiCl.sub.4") near3 precursor)</u>	<u>US-PGPUB;</u> <u>USPAT</u>
<u>14</u>	<u>BRS</u>	<u>L14</u>	<u>4</u>	<u>(ald or (atomic adj layer adj deposition)) same (((silicon adj tetrachloride) or "SiCl.sub.4") near5 precursor)</u>	<u>US-PGPUB;</u> <u>USPAT</u>
<u>15</u>	<u>BRS</u>	<u>L15</u>	<u>1</u>	<u>14 not 13</u>	<u>US-PGPUB;</u> <u>USPAT</u>
<u>16</u>	<u>BRS</u>	<u>L16</u>	<u>0</u>	<u>(ald or (atomic adj layer adj deposition)) same (((silicon adj tetrachloride) or "SiCl.sub.4") near5 precursor)</u>	<u>USOCR;</u> <u>EPO;</u> <u>JPO;</u> <u>DERWE</u> <u>NT;</u> <u>IBM TD</u> <u>B</u>
<u>17</u>	<u>BRS</u>	<u>L17</u>	<u>0</u>	<u>(ald or (atomic adj layer adj deposition)) and (((silicon adj tetrachloride) or "SiCl.sub.4") near5 precursor)</u>	<u>USOCR;</u> <u>EPO;</u> <u>JPO;</u> <u>DERWE</u> <u>NT;</u> <u>IBM TD</u> <u>B</u>
<u>18</u>	<u>BRS</u>	<u>L18</u>	<u>28</u>	<u>(ald or (atomic adj layer adj deposition)) and (((silicon adj tetrachloride) or "SiCl.sub.4") near5 precursor)</u>	<u>US-PGPUB;</u> <u>USPAT</u>